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[165] ***Invited Talk:*** H. Iwai, T. Ohguro, S. Ohmi, "NiSi Salicide Technology for Scaled CMOS," Abstract, European Workshop Materials for Advanced Metallization (MAM2001), p.07.5, March 5-7, 2001 ,Sigtuna, Sweden

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[174] ***Invited Talk:*** H. Iwai, "Silicon technology trend from past to future," IEEE Electron Devices and Solid-State Circuits Society Bangalore Chapter, March 2002, India

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[307] ***Distinguished Lecture:*** Hiroshi iwai, "Past and future of Si integrated circuit technology" Jan. 9, 11 2007, Kashgar Pedagogical Institute , Kashgar & Hotan Pedagogical College, Hotan, China

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[310] ***Distinguished Lecture:***Hiroshi Iwai, "Nano-CMOS Technology and Its Beyond" Feb. 5 , 2007 , National Chiao Tung University, Taiwang

[311] ***Distinguished Lecture:***Hiroshi Iwai, "Nano-CMOS and High-k/metal Gate Technology" Feb.6, 2007, UMC, Taiwang

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[329] ***Golden Jubilee Distinguished Lecture:*** H.Iwai, "Past and Future Half-Centuries for Semiconductor Device Development" Indian Institute of Technology , Bombay, Jan. 11 , 2008, Bombay, India

[330] H.Iwai, "Advanced Logic Technologies with New Materials and Strucures" Inadian Institute of Science, Jan. 18 , 2008, Bangalore, India

[331] ***Distinguished Lecture:***H.Iwai, "Past and Future for Micro-and Nano-Electronics Focusing on Si Integrated Circuits Technology**"** Narula Institute of Technology , Feb. 29, 2008, Kolkata, India

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[358] H.Iwai, "Technology Scaling and Roadmap for 22nm CMOS logic and beyond" Dalian University of Technology, Mini-Colloquium,Oct. 27, 2008, Dalian, China

[359] H.Iwai, "Future of Nano-CMOS after Scaling Limit" Shenyang University of Technology, Mini-Colloquium,Oct. 28, 2008, Shenyang, China

[360] ***Invited Talk:*** H. Iwai, "Introduction of new materials into Si-integrated Circuits" C-MRS, Nov. 23, 2008, South China University of Technology, Guangzhou, China

[361] H. Iwai, "Past and Future of Si integrated Circuit Technology" Xiangtan University, Nov. 24, 2008, Xiangtan, China

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[366] ***Distinguished Lecture:*** H. Iwai, "Roadmap for 22nm Logic CMOS and Beyond" IIT Bombay, Jan. 21, 2009, Bombay, India

[367] ***Distinguished Lecture:*** H. Iwai, "Roadmap for 22nm Logic CMOS and Beyond" Bengal Engineering Science University, Mar. 5 , 2009, Bengal, India

[368] ***Distinguished Lecture:*** H. Iwai, "Downsizing of transistors towards its Limit" Bengal Institute of Technology&Management, Mar. 6 , 2009, Bengal, India

[369] ***Distinguished Lecture:*** H. Iwai, "Roadmap for 22nm Logic CMOS and Beyond" Heritage Institute of Technology, Mar. 9 , 2009, Heritage, India

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[375] ***Invited Talk:*** H. Iwai, "Technology Roadmap for 22nm CMOS and Beyond", IEEE/2nd IEEE International Workshop On Electron Devices And Semiconductor Technology, June 1, 2009, Indian Institute of Technology Bombay, Mumbai, India

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[28] "Future nanoelectronic device technologies - high-k, nanowire and alternative channel", January 13, 2010, IEEE AP & ED Joint MQ, IIT Bombay, Bombay, India
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